

Int'l Appl. No. : PCT/JP2003/016266
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AMENDMENTS TO THE SPECIFICATION

Prior to the first line of the specification on page 1, please insert the following paragraph:

This application is the U.S. National Phase under 35 U.S.C. §371 of International Application PCT/JP2003/016266, filed December 18, 2003, which claims priority to Japanese Patent Application No. 2002-376294, filed December 26, 2002. The International Application was not published under PCT Article 21(2) in English.

Please amend the Claims as follows. Insertions are shown underlined while deletions are struck through.

The paragraph beginning at page 1, line 13:

KrF positive resist compositions, which have been proposed as ideal resist materials for exposure methods using a KrF excimer laser, typically utilize a polyhydroxystyrene-based resin in which a portion of the hydroxyl groups have been protected with acid dissociable dissolution inhibiting groups as the base resin. As the acid dissociable dissolution inhibiting group, so-called acetal groups including chain-like ether groups typified by 1-ethoxyethyl groups, cyclic ether groups typified by tetrahydropyranyl groups, tertiary alkyl groups typified by tert-butyl groups, and tertiary alkoxycarbonyl groups typified by tert-butoxycarbonyl groups are the most commonly used. See Patent References 1-3 below.

The numeral at page 3, line 4:

{0007}

The numeral at page 4, line 8:

{0013}

The numeral at page 8, line 10:

{0028}

The numeral at page 13, line 19:

{0046}